

Correction to “Gate-Induced Intramolecular Charge Transfer in a Tunnel Junction: A Nonequilibrium Analysis”

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The following erratum was found in the published article due to a technical error in which state (10) has not been taken into account, even though its energy falls within the bias window displayed in the article. This erratum has a small quantitative effect on population distribution and current, but it does not affect the conclusions of the original paper.

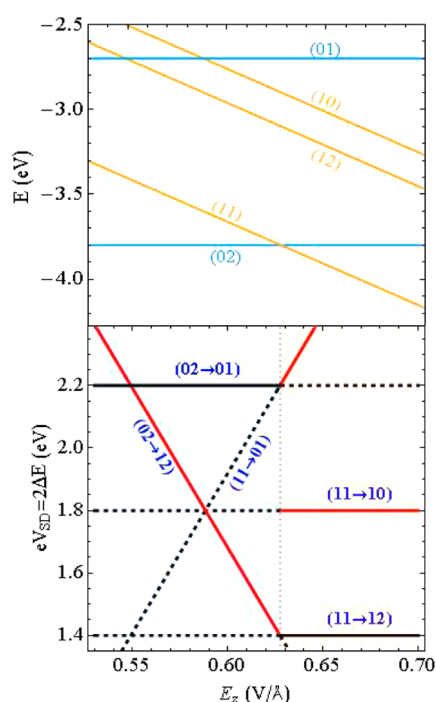


Figure 1. Corrected Figure 4. The state (10) is added to the top panel and the transition (11→10) is added to the bottom panel.

The corrections to the results are as follows:

(1) In Figure 1, we give the correction to Figure 4 of the original article. In the original article, only four states were taken into account, (02), (11), (01), and (12), and therefore only four transition channels were considered. When adding state (10), the (11→10) transition at 1.8 eV becomes possible and has been added to the graph.

(2) In Figure 2, we give the corrections to Figure 6 of the original article. In the population distribution chart, the effect of the additional state (10) is visible as the (11→10) transition. The effect of (10) is noticeable in other regions of the chart. These changes in the population of the charge-carrying states give rise to small changes in the current at high gate fields. The changes are small though and do not alter the appearance of conducting channels. These changes are summarized in Figure 2.

REFERENCES

- (1) Baratz, A.; Galperin, M.; Baer, R. Gate-Induced Intramolecular Charge Transfer in a Tunnel Junction: A Nonequilibrium Analysis. *J. Phys. Chem. C* **2013**, *117*, 10257–10263.

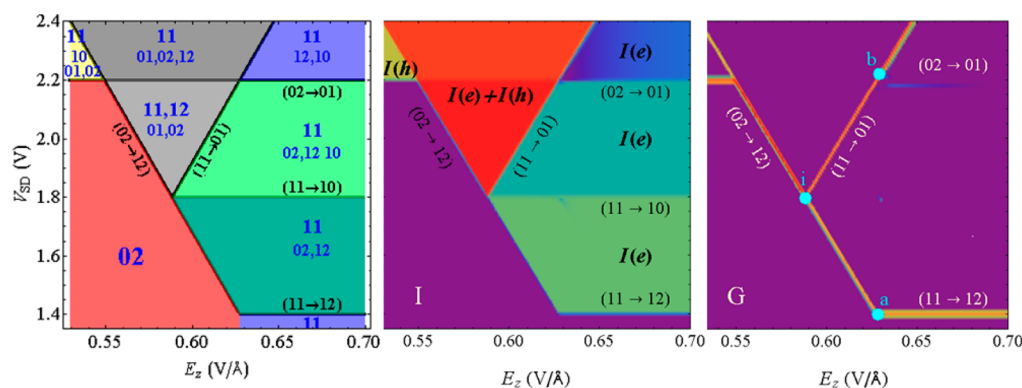


Figure 2. Similar calculation to Figure 6 of the paper¹ taking into account the additional (10) state and the transition (11→10).

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